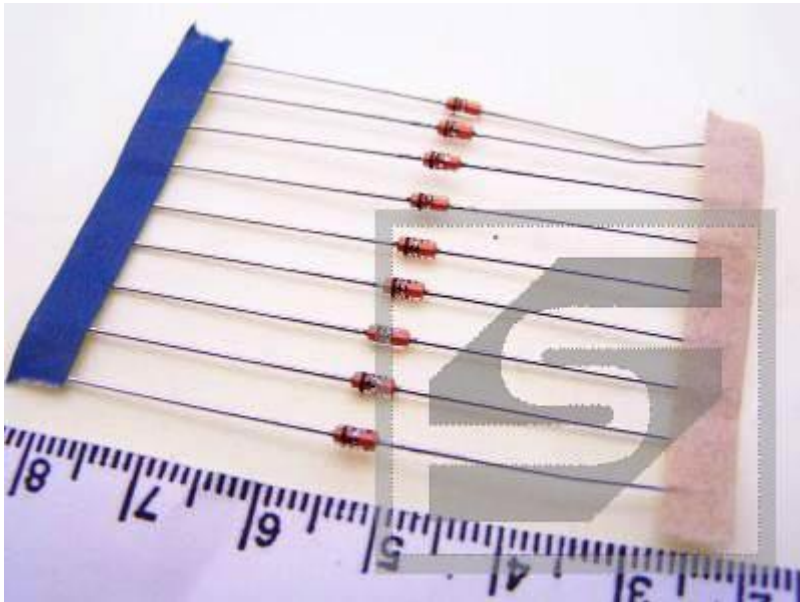




Dioda Schottky BAT85 30V;200mA;4ns DO35 LGE Pbf



Dane techniczne:

Nazwa: BAT85

Typ diody: prostownicza Schottky

Napięcie wsteczne maksymalne: 30V

Napięcie przewodzenia maksymalne: 0.8V

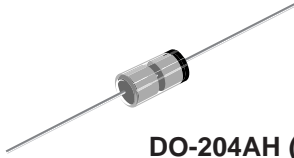
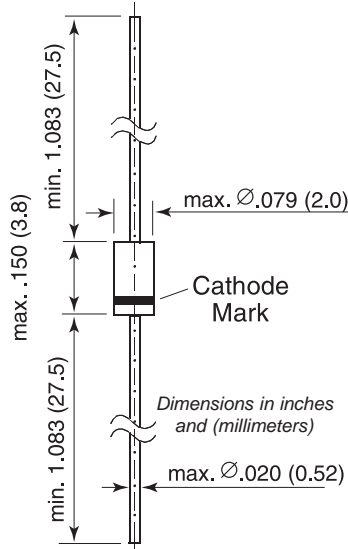
Prąd przewodzenia: 0.2A

Prąd w impulsie maksymalny: 5A

Obudowa: DO35

Montaż: przewlekany(THT)

Schottky Diode


DO-204AH (DO-35 Glass)


Features

- For general purpose applications.
- This diode features low turn-on voltage. This device is protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges
- This diode is also available in the MiniMELF case with type designation BAS85.

Mechanical Data

Case: DO-35 Glass Case

Weight: approx. 0.13g

Packaging Codes/Options:

D7/10K per 13" reel (52mm tape), 20K/box

D8/10K per Ammo tape (52mm tape), 20K/box

Maximum Ratings & Thermal Characteristics Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Value	Unit
Continuous Reverse Voltage	V_R	30	V
Forward Continuous Current at $T_{amb} = 25^\circ\text{C}$	I_F	200 ⁽¹⁾	mA
Peak Forward Current at $T_{amb} = 25^\circ\text{C}$	I_{FM}	300 ⁽¹⁾	mA
Surge Forward Current at $t_p < 1\text{s}$, $T_{amb} = 25^\circ\text{C}$	I_{FSM}	600 ⁽¹⁾	mA
Power Dissipation at $T_{amb} = 65^\circ\text{C}$	P_{tot}	200 ⁽¹⁾	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	430 ⁽¹⁾	$^\circ\text{C/W}$
Maximum Junction Temperature	T_j	125	$^\circ\text{C}$
Ambient Operating Temperature Range	T_A	-65 to +125	$^\circ\text{C}$
Storage Temperature Range	T_S	-65 to +150	$^\circ\text{C}$

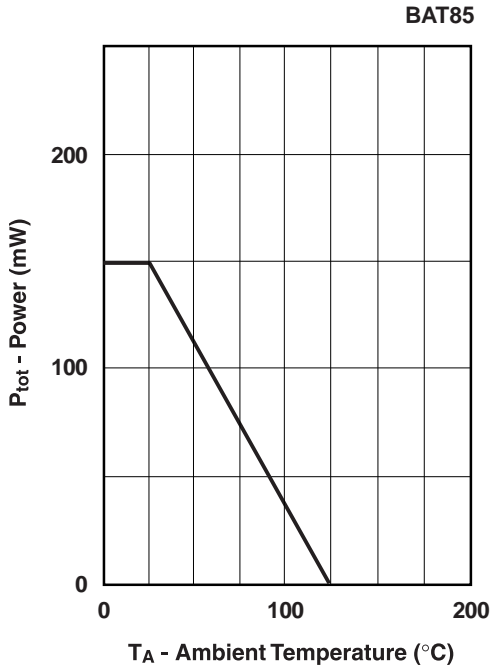
Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Breakdown Voltage	$V_{(BR)R}$	$I_R = 10\mu\text{A}$ (pulsed)	30	—	—	V
Leakage Current	I_R	$V_R = 25\text{V}$	—	—	2	μA
Forward Voltage Pulse Test $t_p < 300\mu\text{s}$, $\delta < 2\%$	V_F	$I_F = 0.1\text{mA}$ $I_F = 1\text{mA}$ $I_F = 10\text{mA}$ $I_F = 30\text{mA}$ $I_F = 100\text{mA}$	— — — — —	— — — 0.5 —	0.24 0.32 0.4 — 0.8	V
Capacitance	C_{tot}	$V_R = 1\text{V}$, $f = 1\text{MHz}$	—	—	10	pF
Reverse Recovery Time	t_{rr}	$I_F = 10\text{mA}$ to $I_R = 10\text{mA}$ to $I_R = 1\text{mA}$	—	—	5	ns

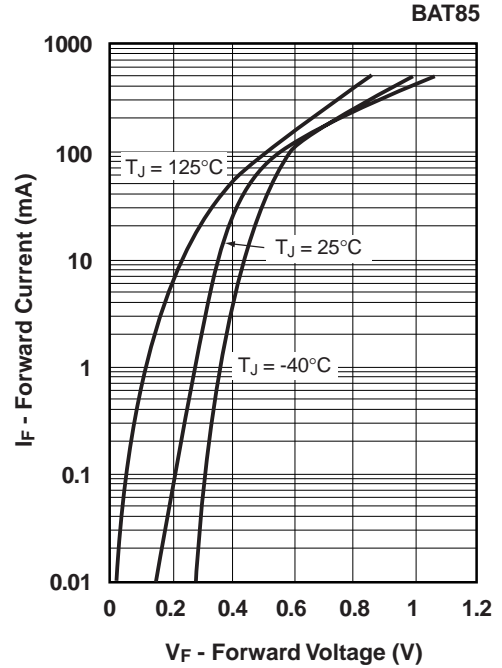
Note: (1) Valid provided that leads at a distance of 4mm from case are kept at ambient temperature

Ratings and Characteristic Curves ($T_A = 25^\circ\text{C}$ unless otherwise noted)

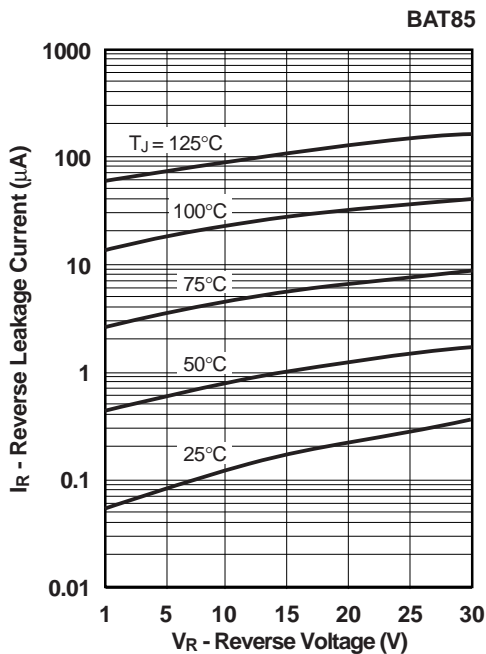
Admissible Power Dissipation vs. Ambient Temperature



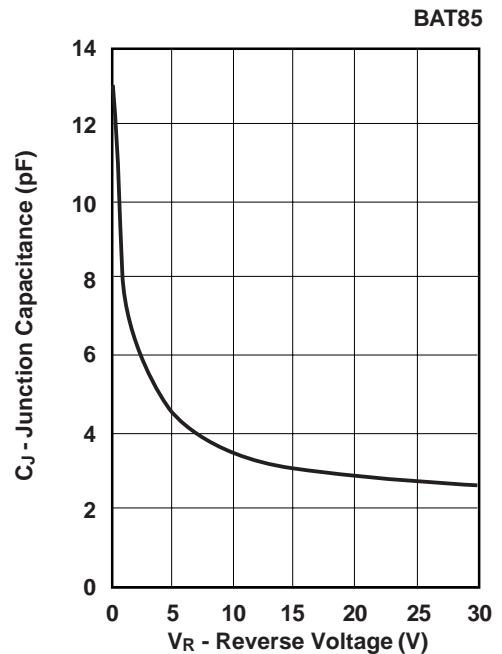
Typical Instantaneous Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance



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www.datasheetcatalog.com

Datasheets for electronics components.